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Description Homogeneous-current 1700V/25A SiC Schottky diode with high surge current, low leakage, no reverse or forward recovery, and high-temperature operation.	V_{RRM} = 1700 V $I_{F}(T_{C} = 135 \ ^{\circ}C) = 46 \ A$ Q_{C} = 271 nC
 Features Temperature-independent fast switching Low reverse leakage current Low V_F at high temperatures Easy paralleling (positive temperature coefficient of V_F) Essential no switching losses High repetitive surge current 	Package RoHS PIN 10 PIN 20 O CASE
 Applications Switch Mode Power Supplies (SMPS) Power Factor Correction Motor Drives Electric vehicles and battery chargers Solar inverters Free-wheeling diode 	Part NumberQSD25HCS170UPackageTO-247-2LMarkingQS

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Maximum Rated Values ($T_c = 25^{\circ}C$ unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions	Note
V _{RRM}	Repetitive Peak Reverse Voltage	1700	V		$\hat{\mathcal{O}}$
V _R	DC Peak Reverse Voltage	1700	V		
		94		$T_c = 25^{\circ}C$	
\mathbf{I}_{F}	Continuous Forward Current	46	А	T _c = 135°C	Fig. 3
	Current	32		$T_c = 150$ °C	
т	Repetitive Peak Forward	151		$T_c = 25^{\circ}C$, $t_P = 10$ ms, Half Sine Pulse	
I _{FRM}	Surge Current	130	Α	$T_{C} = 110$ °C, $t_{P} = 10$ ms, Half Sine Pulse	
т	Non-Repetitive Forward	177		$T_c = 25$ °C, $t_P = 10$ ms, Half Sine Pulse	
I_{FSM}	Surge Current	154	A	$T_{C} = 110^{\circ}C$, $t_{P} = 10$ ms, Half Sine Pulse	
т	Non-Repetitive Forward	1150		$T_{c} = 25^{\circ}C$, $t_{P} = 10\mu s$, Square Wave Pulse	
$I_{F,MAX}$	Surge Current	950	Α	$T_{C} = 110^{\circ}$ C, $t_{P} = 10\mu$ s, Square Wave Pulse	
D	Devue Dissingtion	556		$T_c = 25^{\circ}C$	Fig. 4
P _{tot}	Power Dissipation	241	W	$T_{c} = 110^{\circ}C$	Fig. 4
T ₁	Operating Temperature	-55 to	°C 🔹		
IJ		+175	C		
T _{stg}	Storage Temperature	-55 to	°C		
' stg		+175		×	
	TO-247 Mounting Torque	1 8.8	Nm Ibf-in	M3 Screw 6-32 Screw	

Electrical Characteristics $(T_j = 25^{\circ}C)$

		Value					
Symbol	Parameter	Min.	Тур.	Max.	Unit	Test Conditions	Note
N			1.4	1.9	v	I _F = 25A, T _J = 25°C	Fig. 1
V _F	Forward Voltage		2.2	2.7	V	I _F = 25A, T _J = 175°C	Fig. 1
.	Devenue Connect		3	10		V _R = 1700V, T _J = 25°C	Fig. 2
I _R	Reverse Current		138	250	μA	V _R = 1700V, T _J = 175°C	Fig. 2
Q _c	Total Capacitive Charge		271		nC	$V_R = 1200V, I_F = 25A$ di/dt = 200A/us, T _J = 25°C	Fig. 5
			2822			$V_{R} = 0V, T_{J} = 25^{\circ}C, f = 1MHz$	
С	Total Capacitance		120		pF	$V_{R} = 800V, T_{J} = 25^{\circ}C, f = 1MHz$	Fig. 6
			117			V _R = 1200V, T _J = 25°C,f = 1MHz	
Ec	Capacitance Stored Energy		107		μJ	V _R = 0~1200 V	Fig. 7

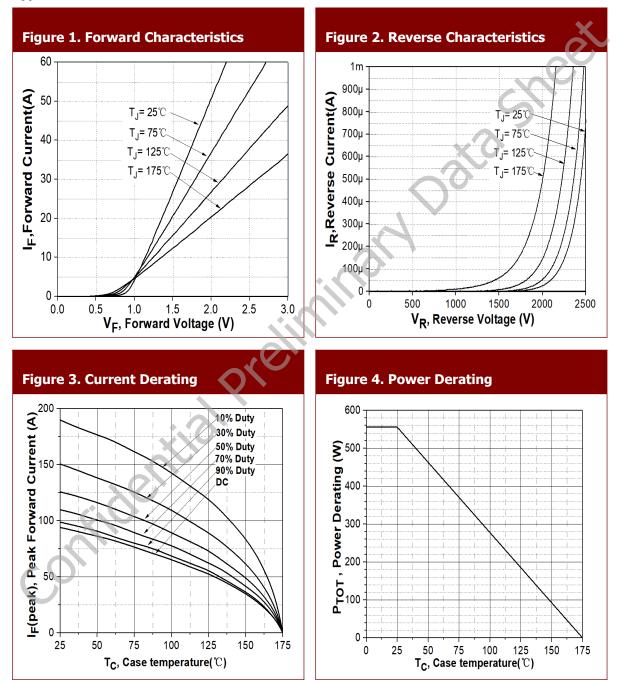
Thermal Characteristics

Symbol	Parameter	Value	Unit	Note
R _{eJC}	Thermal Resistance (Junction to Case)	0.27	°C/W	Fig. 8



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Typical Performance

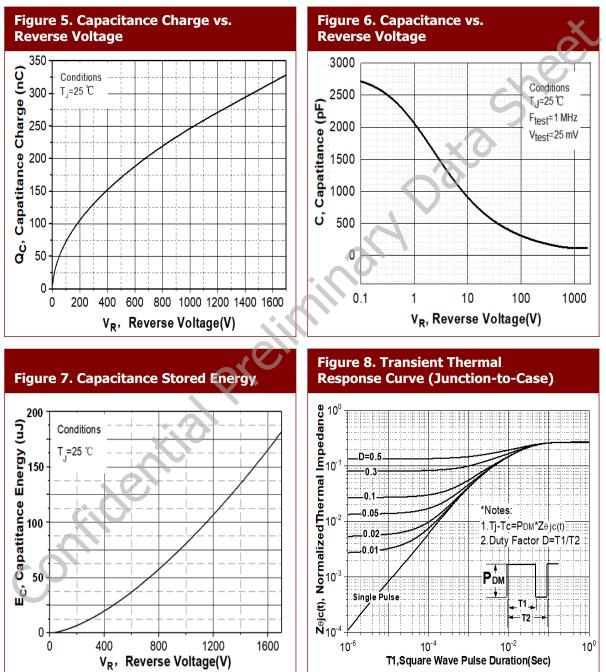


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Typical Performance



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Package Dimensions					K
Package TO-247-2L	POS	Inc	hes	Millin	neters
	FUS	Min	Max	Min	Max
	A	.190	.205	4.70	5.31
	2 A1	.087	.102	2.21	2.59
	A2	.059	.098	1.50	2.49
	b	.039	.055	0.99	1.40
	b2	.065	.094	1.65	2.39
	с	.015	.035	0.38	0.89
	D	.819	.845	20.80	21.46
	D1	.515	-	13.08	-
	D2	.020	.053	0.51	1.35
	E	.620	.640	15.49	16.26
	E1	.530	-	13.46	-
	E2	.135	.157	3.43	3.99
	е	.2	14	5.	44
	ØК	.0	10	0.	25
	L	.780	.800	19.81	20.32
← [← 2x b2 c → ← ← A1	L1	-	.177	-	4.50
→ 2x b	ØP	.140	.144	3.56	3.66
<u>↓</u> 10 [•]	ØP1	.278	.291	7.06	7.39
	Q	.212	.244	5.38	6.20
	S	.2	43	6.	17
3'	w	-	.006	-	0.15

Recommended Solder Pad Layout



Part Number	Package	Marking
QSD25HCS170U	TO-247-2L	QS